The effect of atomic-scale defects and dopants on Graphene electronic structure

Rocco Martinazzo

Dip. di Chimica-Fisica e Elettrochimica
Universita' degli Studi di Milano, Milan, Italy

GraphITA
GSNL, Assergi (L'Aquila), May 15th - 18th 2011

Outline

1. Introduction
2. Hydrogen adsorption
3. Bandgap engineering

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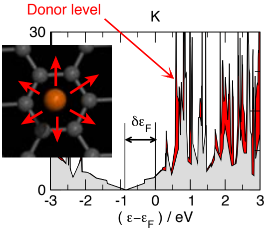
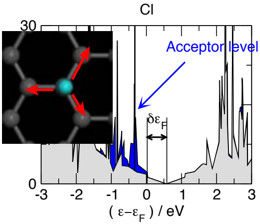
3. Bandgap engineering

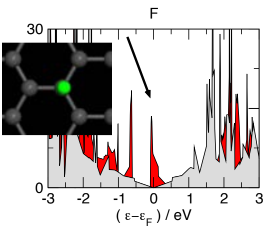
Ionic binding





- DOSs are unchaged except for donor/acceptor levels
- electron / hole doping
- Atomic species are mobile
- Li, Na, K, Cs.. vs Cl,Br,I,..

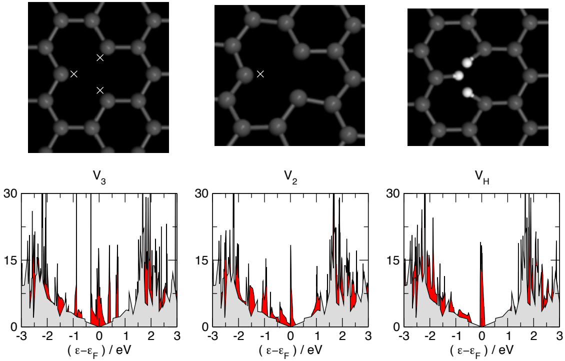
Covalent binding



- Midgap states show up in the DOSs
- Atomic species are immobile
- H, F, OH, CH_3, etc. behave similarly to vacancies

See e.g., T. O. Wehling, M. I. Katsnelson and A. I. Lichtenstein, *Phys. Rev. B* **80**, 085428 (2008)

Vacancies *vs* adatoms

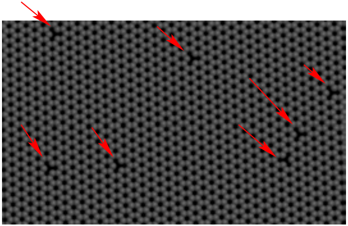


Unrelaxed   Relaxed   Saturated

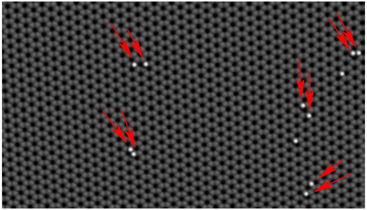
See e.g., F. Banhart, J. Kotakoski, A. V. Krasheninnikov, *ACS Nano* **5**, 26 (2011)

Vacancies *vs* adatoms

High-energy e$^-$/ion beams
$\Rightarrow$ **Random** arrangement



Low-energy beams (kinetic control)
$\Rightarrow$ **Clustering** due to preferential sticking



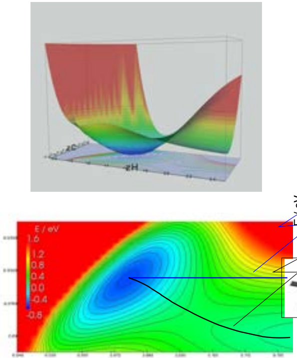
Outline

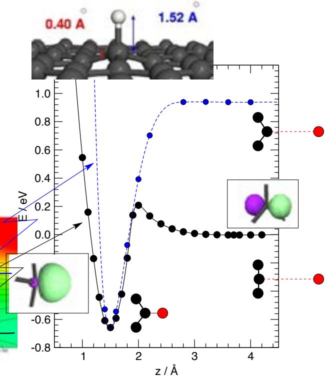
Hydrogen chemisorption on graphene

- Sticking is thermally activated[1,2]
- Midgap states are generated upon sticking
- Diffusion does not occur[3,4]
- Preferential sticking and clustering[3,5,6]

[1] L. Jeloaica and V. Sidis, *Chem. Phys. Lett.* **300**, 157 (1999)
[2] X. Sha and B. Jackson, *Surf. Sci.* **496**, 318 (2002)
[3] L. Hornekaer *et al.*, *Phys. Rev. Lett.* **97**, 186102 (2006)
[4] J. C. Meyer *et al.*, *Nature* **454**, 319 (2008)
[5] A. Andree *et al.*, *Chem. Phys. Lett.* **425**, 99 (2006)
[6] L. Hornekaer *et al.*, *Chem. Phys. Lett.* **446**, 237 (2007)

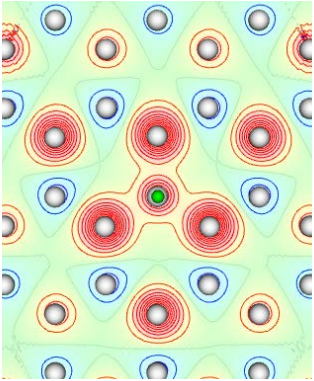
Sticking



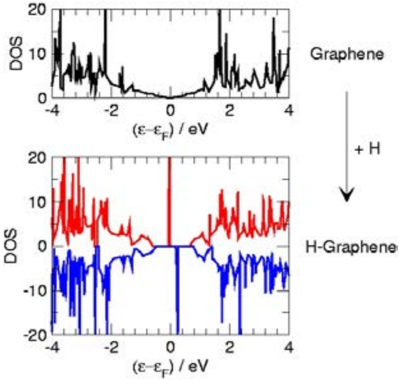


L. Jeloaica and V. Sidis, *Chem. Phys. Lett.* **300**, 157 (1999)
X. Sha and B. Jackson, *Surf. Sci.* **496**, 318 (2002)

Midgap states



..*patterned* spin-density



Midgap states

$$H^{TB} = \sum_{\sigma,ij}(t_{ij}a^{\dagger}_{i,\sigma}b_{j,\sigma} + t_{ji}b^{\dagger}_{j,\sigma}a_{i,\sigma})$$

Electron-hole symmetry

$$b_i \to -b_i \Longrightarrow \mathbf{h} \to -\mathbf{h}$$

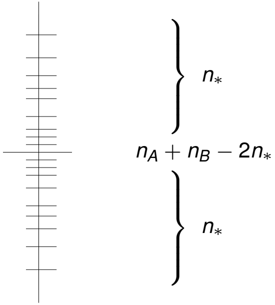
if ϵ_i is eigenvalue and

$c_i^{\dagger} = \sum_i \alpha_i a_i^{\dagger} + \sum_j \beta_j b_j^{\dagger}$ eigenvector

$$\Downarrow$$

$-\epsilon_i$ is also eigenvalue and

$c_i^{\prime\dagger} = \sum_i \alpha_i a_i^{\dagger} - \sum_j \beta_j b_j^{\dagger}$ is eigenvector



Midgap states

$$H^{TB} = \sum_{\tau,ij}(t_{ij}a^{\dagger}_{i,\tau}b_{j,\tau} + t_{ji}b^{\dagger}_{j,\tau}a_{i,\tau})$$

Theorem

If $n_A > n_B$ there exist (at least) $n_I = n_A - n_B$ "midgap states" with vanishing components on B sites

Proof.

$$\begin{bmatrix} \mathbf{0} & \mathbf{T}^{\dagger} \\ \mathbf{T} & \mathbf{0} \end{bmatrix} \begin{bmatrix} \boldsymbol{\alpha} \\ \boldsymbol{\beta} \end{bmatrix} = \begin{bmatrix} \mathbf{0} \\ \mathbf{0} \end{bmatrix} \text{ with } \mathbf{T}\ n_B x n_A(\ > n_B)$$

$$\Longrightarrow \mathbf{T}\boldsymbol{\alpha} = \mathbf{0} \text{ has } n_A - n_B \text{ solutions}$$

□

Midgap states

$$H^{Hb} = \sum_{\tau,ij}(t_{ij}a^{\dagger}_{i,\tau}b_{j,\tau} + t_{ji}b^{\dagger}_{j,\tau}a_{i,\tau}) + U\sum_i n_{i,\tau}n_{i,-\tau}$$

Theorem

If $U > 0$, the ground-state at half-filling has

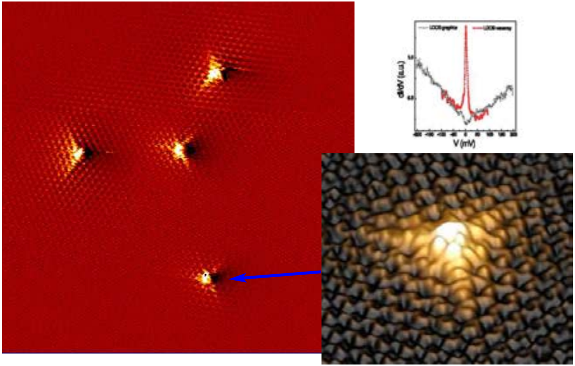
$$S = |n_A - n_B|/2 = n_I/2$$

Proof.

E.H. Lieb, *Phys. Rev. Lett.* **62**, 1201 (1989) □

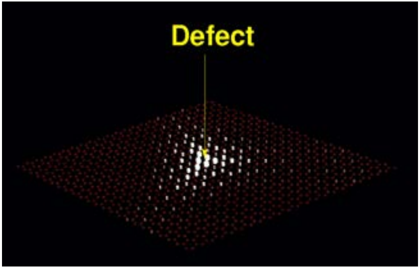
...basically, we can apply Hund's rule to previous result

Midgap states for isolated “defects”



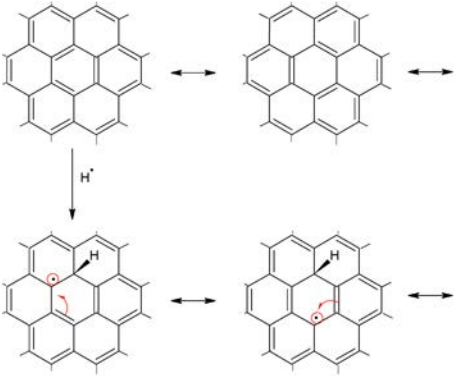
M.M. Ugeda, I. Brihuega, F. Guinea and J.M. Gomez-Rodriguez, *Phys. Rev. Lett.* **104**, 096804 (2010)

Midgap states for isolated “defects”

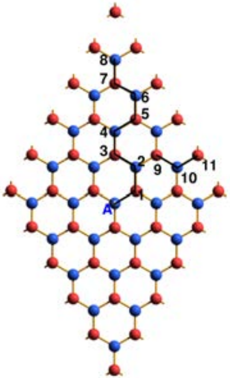


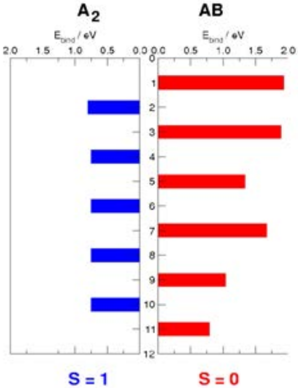
$\psi(x, y, z) \sim 1/r$

V. M. Pereira *et al.*, *Phys. Rev. Lett.* **96**, 036801 (2006); *Phys. Rev. B* **77**, 115109 (2008)

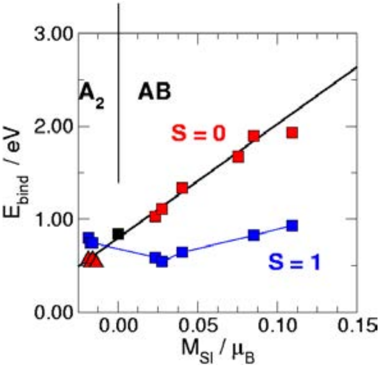


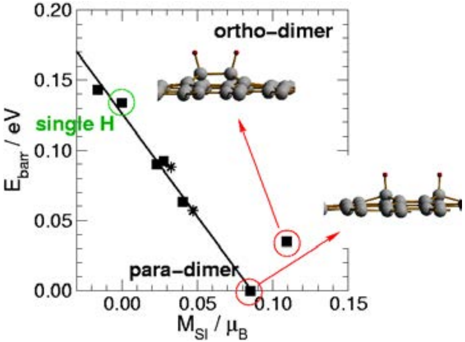
Dimers


8
7
6
5
4
3
2
9
11
10
1
A


A2
AB
E_bind / eV
E_bind / eV
2.0 1.5 1.0 0.5 0.0
0.0 0.5 1.0 1.5 2.0
0
1
2
3
4
5
6
7
8
9
10
11
12
S = 1
S = 0

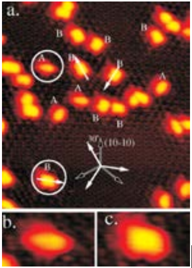
Dimers



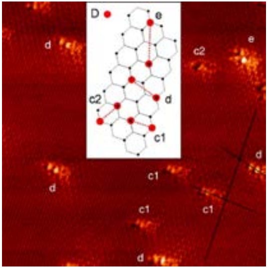


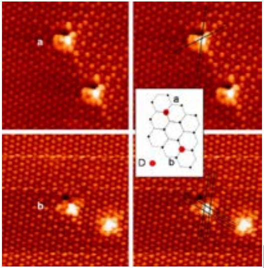
S. Casolo, O.M. Lovvik, R. Martinazzo and G.F. Tantardini, *J. Chem. Phys.* **130** 054704 (2009)

Dimers



[1]



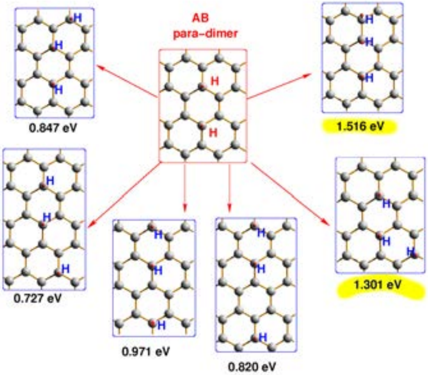


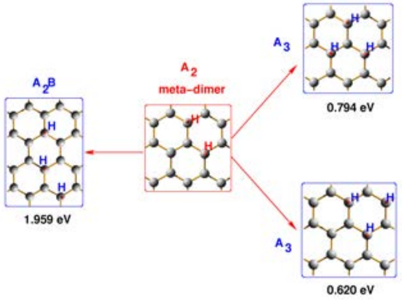
[2]

[1] L. Hornekaer, Z. Sljivancanin, W. Xu, R. Otero, E. Rauls, I. Stensgaard, E. Laegsgaard, B. Hammer and F. Besenbacher. *Phys. Rev. Lett.* **96** 156104 (2006)

[2] A. Andree, M. Le Lay, T. Zecho and J. Kupper, *Chem. Phys. Lett.* **425** 99 (2006)

Clusters

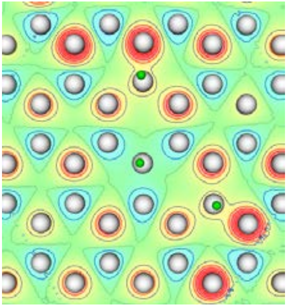




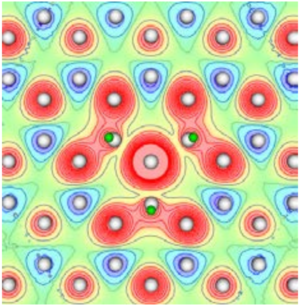
$$\mu = 1\mu_B \Rightarrow \mu = 2\mu_B \Rightarrow \mu = 3\mu_B$$

Clusters

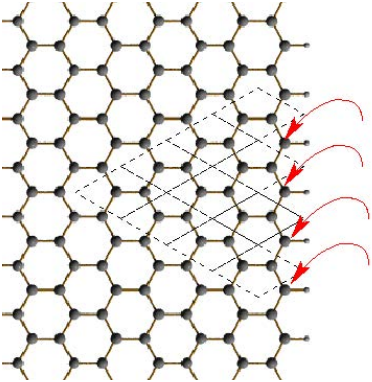
A_2B



A_3

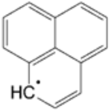


Role of edges

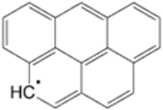


- *zig-zag* edge sites have enhanced hydrogen affinity
- geometric effects can be investigated in small graphenes

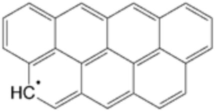
Role of edges



perinaftenile / fenalene

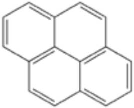


benzo[cd]pirenile

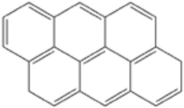


7 - PAH

imbalanced ‘PAHs’



pirene



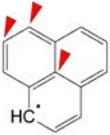
dibenzo[def,mno]crisene / antrantrene

benzo[ghi]perilene

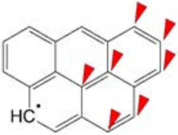
coronene

balanced PAHs

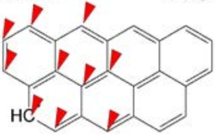
Role of edges



perinaftenile / fenalene



benzo[cd]pirenile



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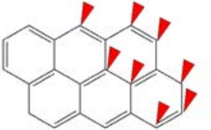

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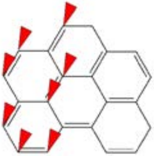
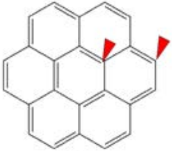


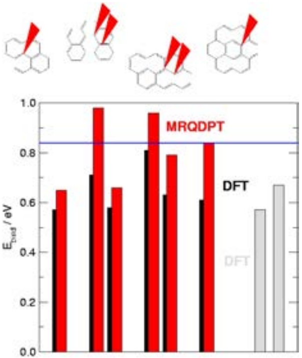
benzo[ghi]perilene

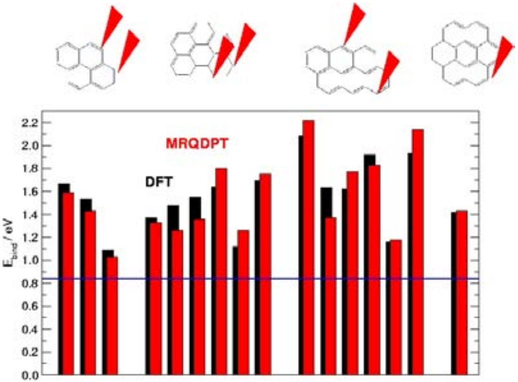


coronene

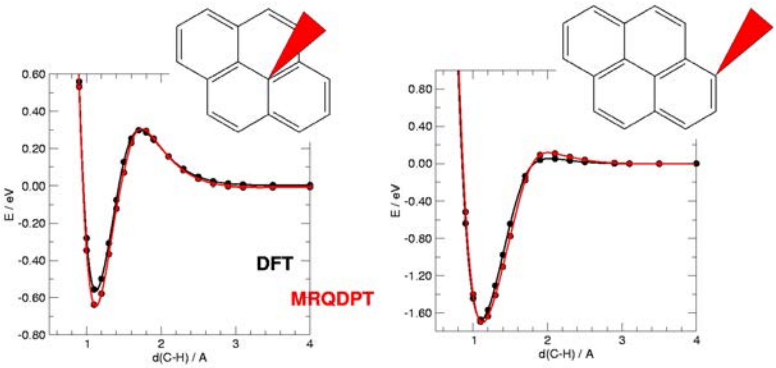
balanced PAHs

Role of edges: graphenic *vs* edge sites





Role of edges: graphenic *vs* edge sites



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Band-gap opening

- **Electron confinement**: nanoribbons, (nanotubes),etc.
- **Symmetry breaking**: epitaxial growth, deposition, etc.
- **Symmetry preserving**: “supergraphenes”

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e-*h* symmetry

$$H^{TB} = \sum_{\sigma,ij} (t_{ij} a^{\dagger}_{i,\sigma} b_{j,\sigma} + t_{ji} b^{\dagger}_{j,\sigma} a_{i,\sigma})$$

Electron-hole symmetry

$$b_i \rightarrow -b_i \Longrightarrow \mathbf{h} \rightarrow -\mathbf{h}$$

if ϵ_i is eigenvalue and

$c^{\dagger}_i = \sum_i \alpha_i a^{\dagger}_i + \sum_j \beta_j b^{\dagger}_j$ eigenvector

$$\Downarrow$$

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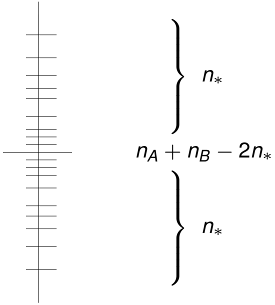
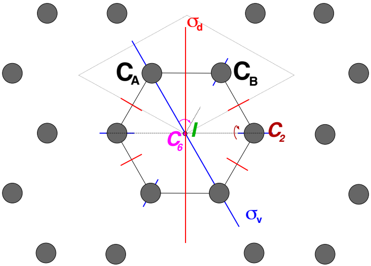


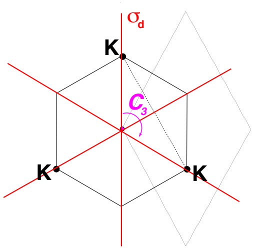
Spatial symmetry

r-space



$G_0 = D_{6h}$

k-space

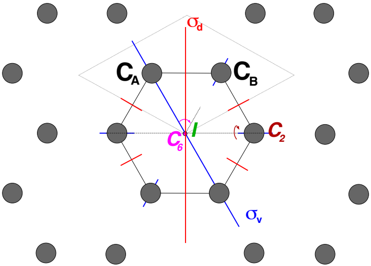


$G(\mathbf{k}) = \{g \in G_0 | g\mathbf{k} = \mathbf{k} + \mathbf{G}\}$

$\Rightarrow G(\mathbf{K}) = D_{3h}$

Spatial symmetry

r-space



$G_0 = D_{6h}$

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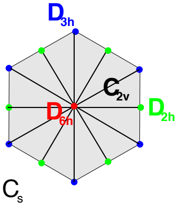
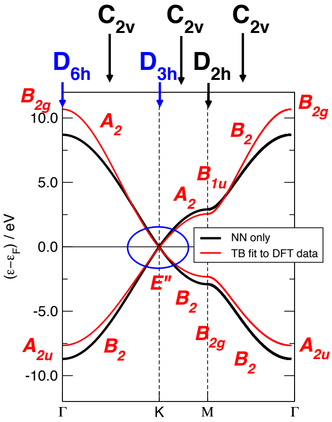


$$G(\mathbf{k}) = \{g \in G_0 | g\mathbf{k} = \mathbf{k} + \mathbf{G}\}$$
$$\Rightarrow G(\mathbf{K}) = D_{3h}$$

Spatial symmetry



$$|A_{\mathbf{k}}\rangle = \frac{1}{\sqrt{N_{BK}}} \sum_{\mathbf{R}\in BK} e^{-i\mathbf{kR}} |A_{\mathbf{R}}\rangle$$

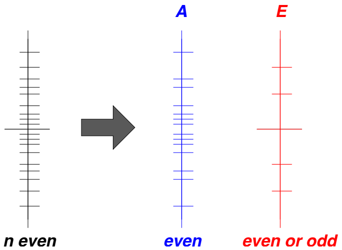
$$|B_{\mathbf{k}}\rangle = \frac{1}{\sqrt{N_{BK}}} \sum_{\mathbf{R}\in BK} e^{-i\mathbf{kR}} |B_{\mathbf{R}}\rangle$$

$$\langle r|A_{\mathbf{R}}\rangle = \phi_{pz}(\mathbf{r} - \mathbf{R})$$

For $\mathbf{k} = \mathbf{K}$ (or $\mathbf{K}'$)

- $\{|A_{\mathbf{k}}\rangle, |B_{\mathbf{k}}\rangle\}$ span the E'' irrep of D_{3h}
- Degeneracy is lifted at first order (no i symmetry in D_{3h})

Spatial and *e-h* symmetry



Lemma

e-h symmetry holds within each kind of symmetry species (A, E, ..)

Theorem

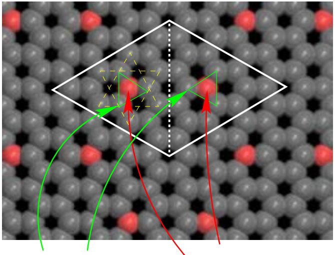
For any bipartite lattice at half-filling, if the number of E irreps is odd at a special point, there is a degeneracy at the Fermi level, i.e. $E_{gap} = 0$

A simple recipe

- Consider *nxn* graphene superlattices (i.e. $G = D_{6h}$): degeneracy is expected at Γ, K
- Introduce p_z vacancies while preserving point symmetry
- Check whether it is possible to turn the number of E irreps to be even both at Γ and at K

Counting the number of E irreps

$$n = 4$$



Γ: 2A + 2E
K: 2A + 2E

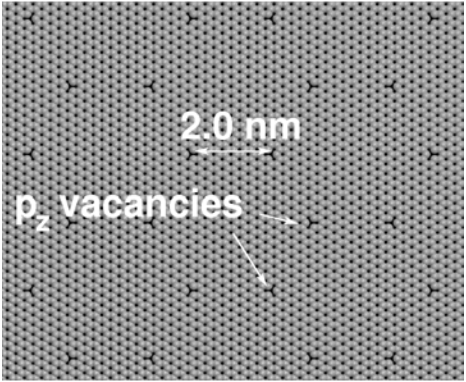
Γ: 2A
K: E

Γ	A	E
$\bar{0}_3$	$2m^2$	$2m^2$
$\bar{1}_3$	$2(3m^2+2m+1)$	$2(3m^2+2m)$
$\bar{2}_3$	$2(3m^2+4m+2)$	$2(3m^2+4m+1)$
K_n	A	E
$\bar{0}_3$	$2m^2$	$2m^2$
$\bar{1}_3$	$2m(3m+2)$	$2m(3m+2)+1$
$\bar{2}_3$	$2(3m^2+4m+1)$	$2(3m^2+4m+1)+1$

$$\Rightarrow n = 3m+1, 3m+2,\ m \in \mathbb{N}$$

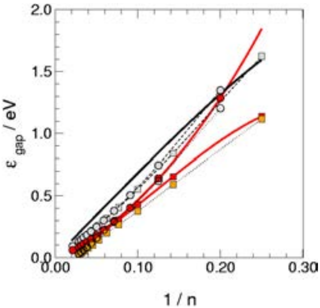
An example

$(14,0)$-honeycomb



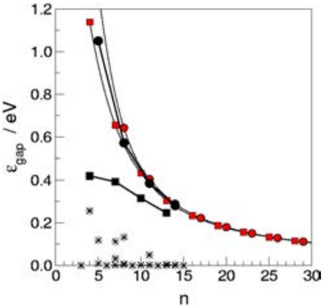
Band-gap opening..

Tight-binding



$$\epsilon_{gap}(K) \sim 2t\sqrt{1.683}/n$$

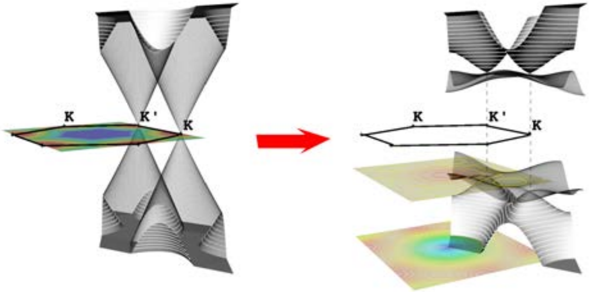
DFT



R. Martinazzo, S. Casolo and G.F. Tantardini, *Phys. Rev. B*, **81** 245420 (2010)

..and Dirac cones

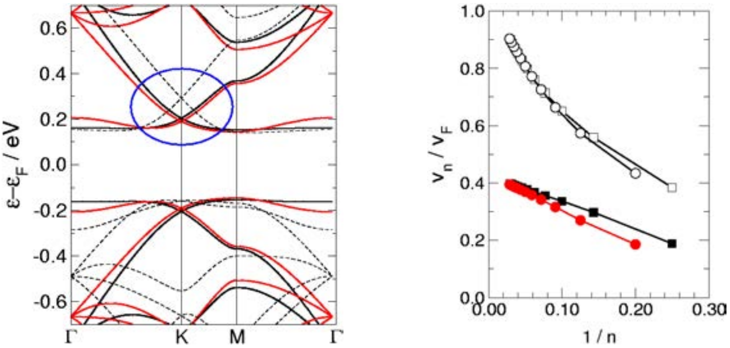
..not only: as degeneracy may still occur at $\epsilon \neq \epsilon_F$
new Dirac points are expected



graphene (4x4) (4,0)–honeycomb

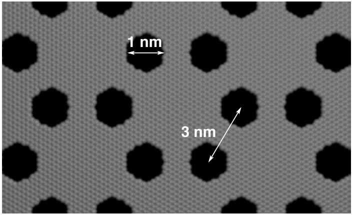
..and Dirac cones

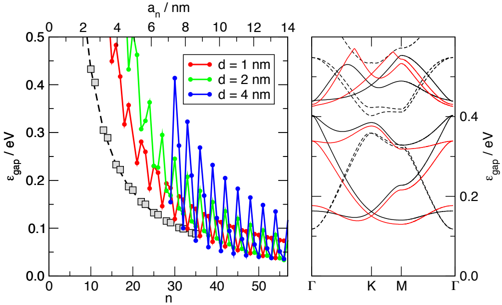
..not only: as degeneracy may still occur at $\epsilon \neq \epsilon_F$
new Dirac points are expected



Antidot superlattices

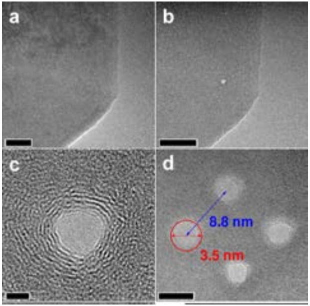
...the same holds for honeycomb antidots



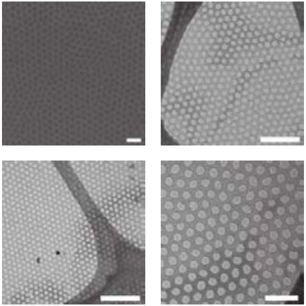


Antidot superlattices

...the same holds for honeycomb antidots



M. D. Fishbein and M. Drndic, *Appl. Phys. Lett.* **93**, 113107 (2008)
T. Shen *et al.* *Appl. Phys. Lett.* **93**, 122102 (2008)



J. Bai *et al.* *Nature Nantotech.* **5**, 190 (2010)

Summary

- Covalently bound species generate midgap species upon bond formation
- Midgap states affect chemical reactivity
- Thermodynamically and kinetically favoured configurations minimize sublattice imbalance
- Symmetry *breaking* is not necessary to open a gap

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http://users.unimi.it/cdtg

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Thank you for your attention!